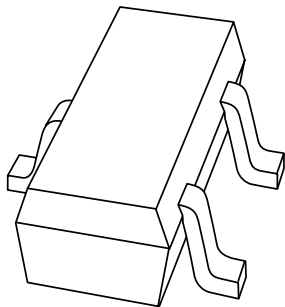


DATA SHEET



PRF949 UHF wideband transistor

Product specification
Supersedes data of 1999 Nov 02

2000 Apr 03

UHF wideband transistor

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FEATURES

- Small size
- Low noise
- Low distortion
- High gain
- Gold metallization ensures excellent reliability.

APPLICATIONS

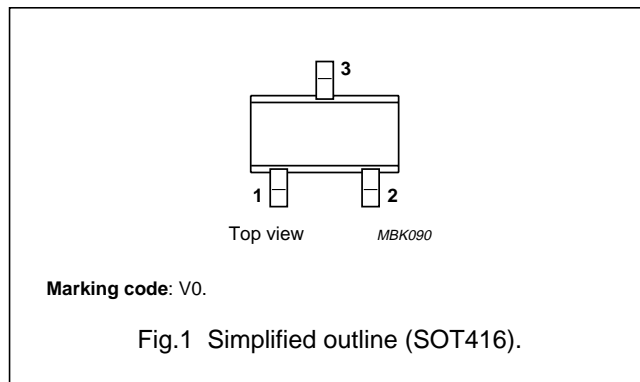
- Communication and instrumentation systems.

DESCRIPTION

Silicon NPN transistor in a surface mount 3-pin SOT416 (SC-75) package. The transistor is primarily intended for wideband applications in the GHz range in the RF front end of analog and digital cellular telephones, cordless phones, radar detectors, pagers and satellite TV-tuners.

PINNING SOT416 (SC-75)

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
C_{re}	feedback capacitance	$I_C = 0$; $V_{CB} = 6$ V; $f = 1$ MHz	–	0.3	–	pF
f_T	transition frequency	$I_C = 15$ mA; $V_{CE} = 6$ V; $f_m = 1$ GHz	7	9	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 15$ mA; $V_{CE} = 6$ V; $T_{amb} = 25$ °C; $f = 1$ GHz	–	16	–	dB
NF	noise figure	$\Gamma_S = \Gamma_{opt}$; $I_C = 5$ mA; $V_{CE} = 6$ V; $f = 1$ GHz	–	1.5	2.5	dB
P_{tot}	total power dissipation	$T_s = 75$ °C; note 1	–	–	150	mW
$R_{th\ j-s}$	thermal resistance from junction to soldering point		–	–	500	K/W

Note

1. T_s is the temperature at the soldering point of the collector pin.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	10	V
V_{EBO}	emitter-base voltage	open collector	–	1.5	V
I_C	collector current (DC)		–	50	mA
$I_{C(AV)}$	average collector current		–	50	mA
P_{tot}	total power dissipation	$T_s = 75\text{ °C}$; note 1	–	150	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

- T_s is the temperature at the soldering point of the collector pin.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	500	K/W

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CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise specified.

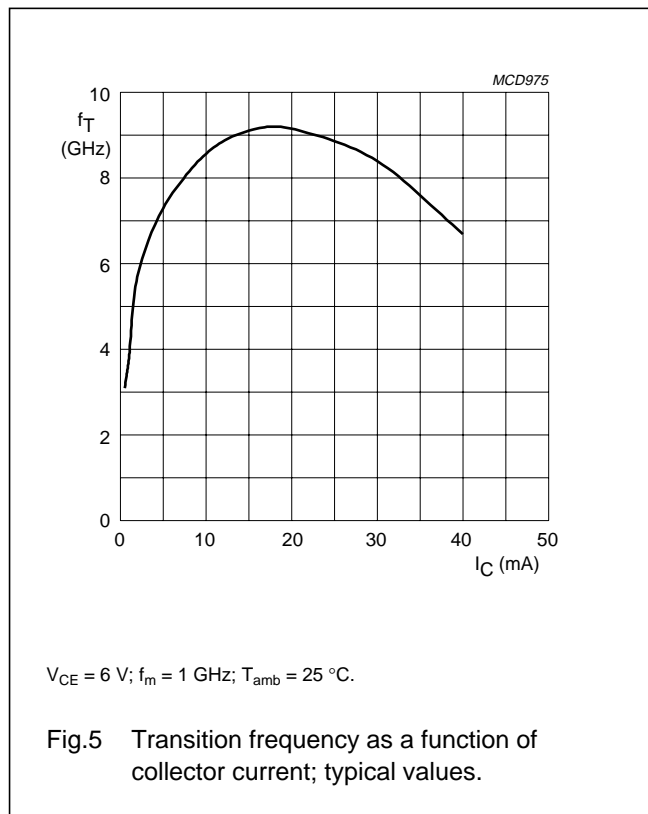
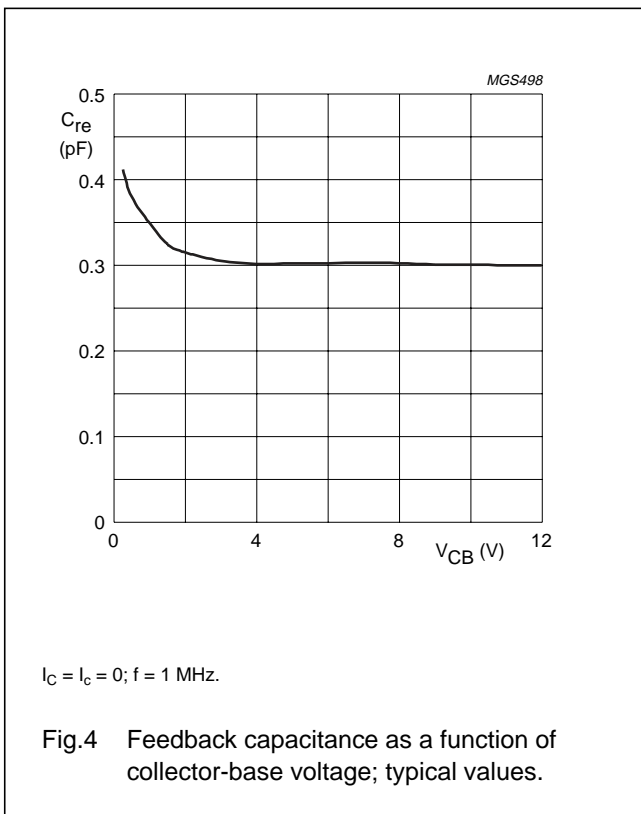
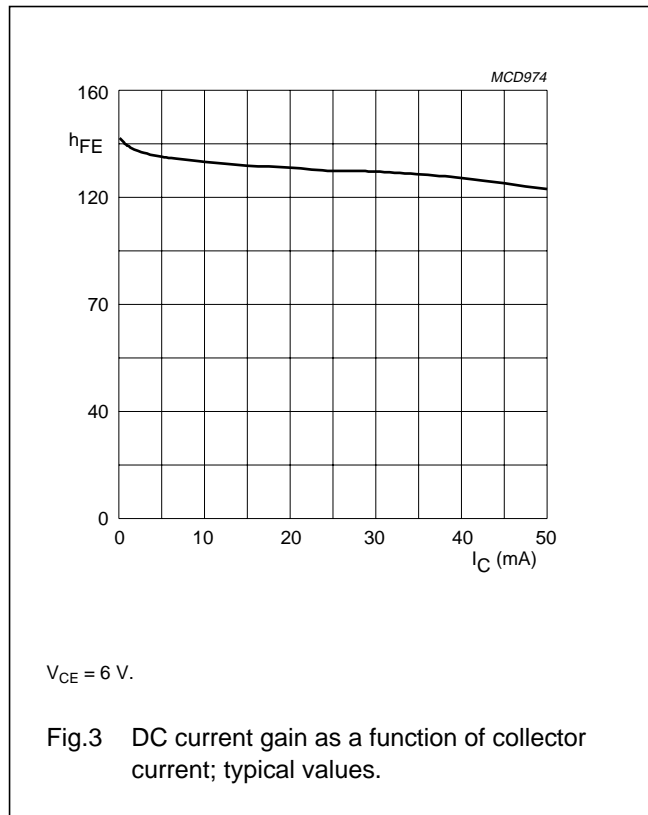
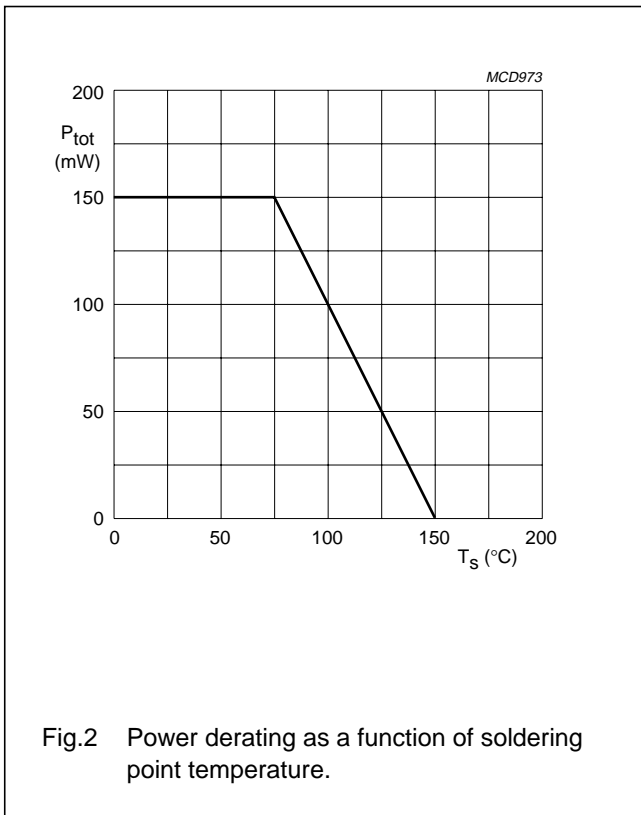
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
DC characteristics						
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 100\ \mu\text{A}; I_E = 0$	20	–	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 100\ \mu\text{A}; I_B = 0$	10	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 10\ \mu\text{A}; I_C = 0$	1.5	–	–	V
V_{BEF}	forward base-emitter voltage	$I_E = 25\ \text{mA}$	–	–	1.05	V
I_{CBO}	collector-base leakage current	$V_{CB} = 10\ \text{V}; I_E = 0$	–	–	100	nA
I_{EBO}	emitter-base leakage current	$V_{EB} = 1\ \text{V}; I_C = 0$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 5\ \text{mA}; V_{CE} = 6\ \text{V}$	100	150	200	
		$I_C = 15\ \text{mA}; V_{CE} = 6\ \text{V}$	–	150	–	
AC characteristics						
C_{re}	feedback capacitance	$I_C = 0; V_{CB} = 6\ \text{V}; f = 1\ \text{MHz}$	–	0.3	–	pF
f_T	transition frequency	$I_C = 15\ \text{mA}; V_{CE} = 6\ \text{V}; f_m = 1\ \text{GHz}$	7	9	–	GHz
$ S_{21} ^2$	insertion gain	$I_C = 15\ \text{mA}; V_{CE} = 6\ \text{V}; f = 1\ \text{GHz}$	13	15	–	dB
G_{UM}	maximum unilateral power gain; note 1	$I_C = 15\ \text{mA}; V_{CE} = 6\ \text{V}; T_{amb} = 25\text{ °C}; f = 1\ \text{GHz}$	–	16	–	dB
		$I_C = 15\ \text{mA}; V_{CE} = 6\ \text{V}; T_{amb} = 25\text{ °C}; f = 2\ \text{GHz}$	–	10	–	dB
NF	noise figure	$\Gamma_S = \Gamma_{opt}; I_C = 5\ \text{mA}; V_{CE} = 6\ \text{V}; f = 1\ \text{GHz}$	–	1.5	2.5	dB
		$\Gamma_S = \Gamma_{opt}; I_C = 5\ \text{mA}; V_{CE} = 6\ \text{V}; f = 2\ \text{GHz}$	–	2.1	–	dB

Note

1. G_{UM} is the maximum unilateral power gain, assuming s_{12} is zero. $G_{UM} = 10 \log \frac{|s_{21}|^2}{(1 - |s_{11}|^2)(1 - |s_{22}|^2)}$ dB

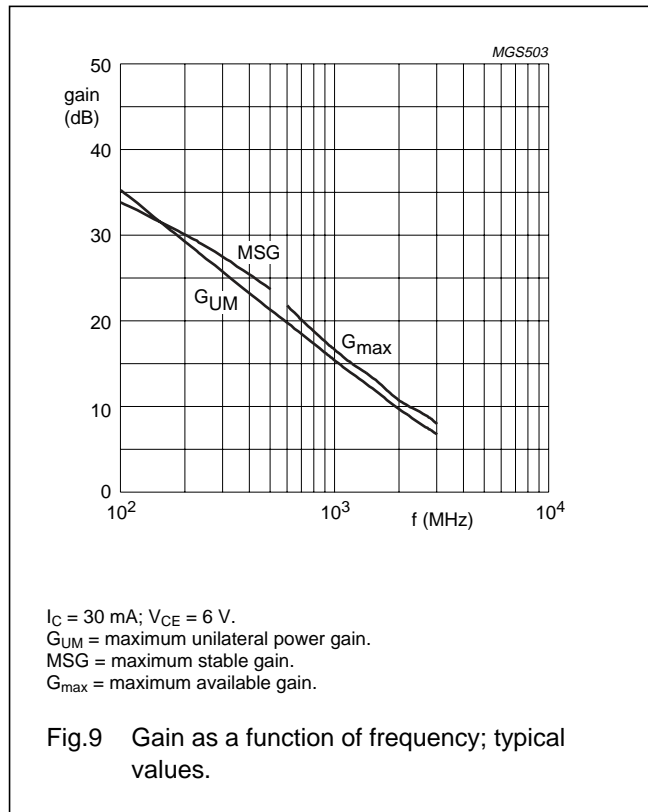
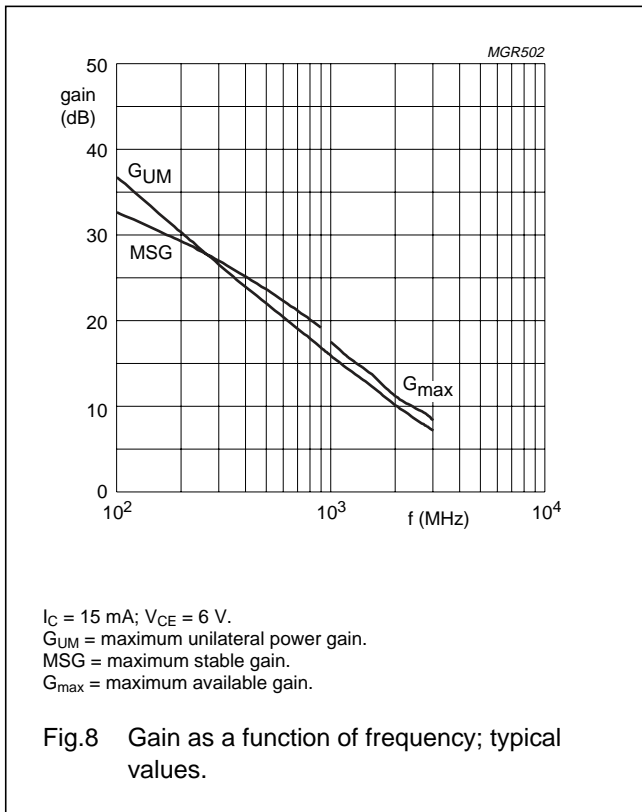
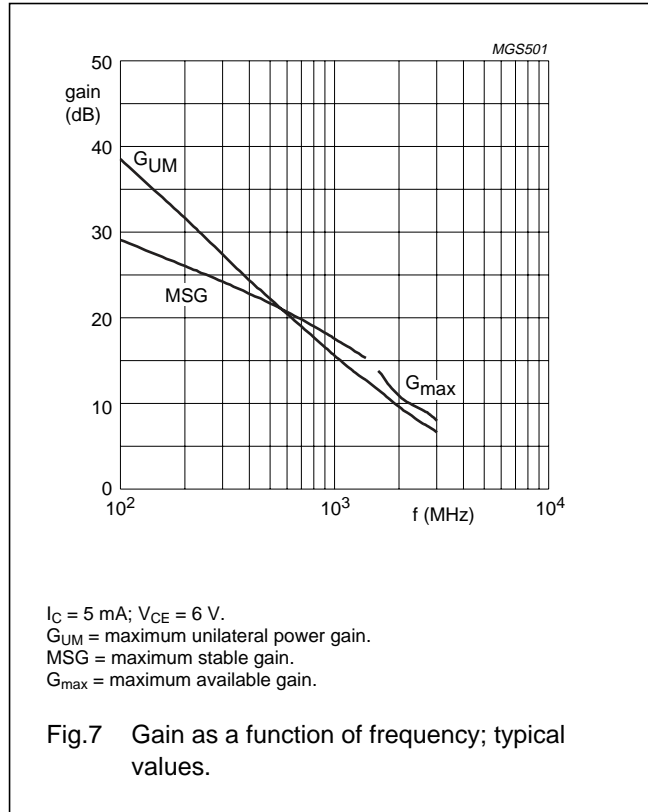
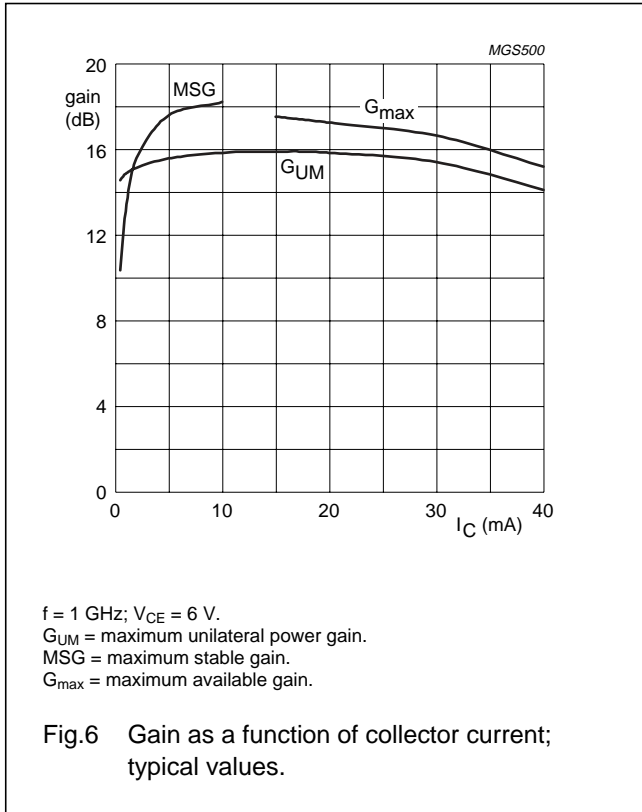
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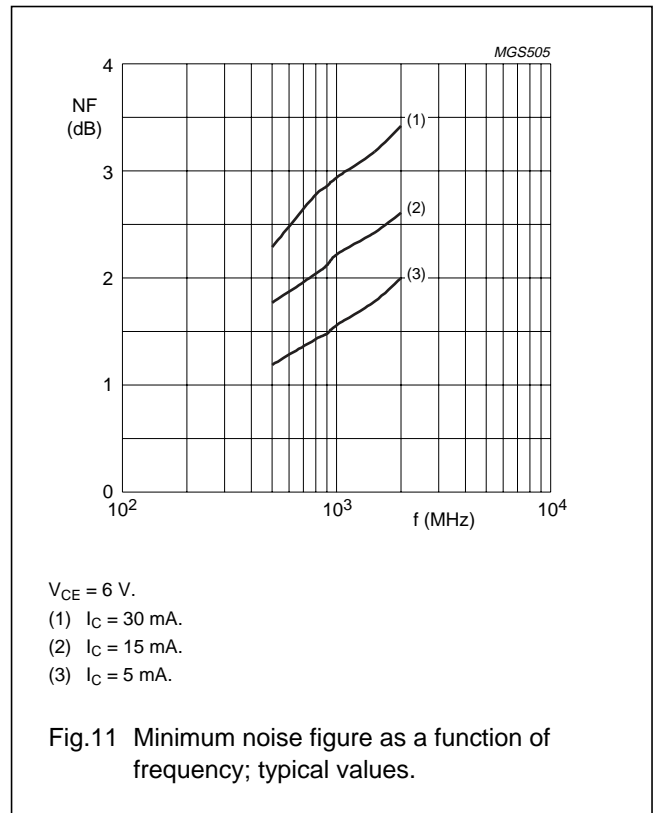
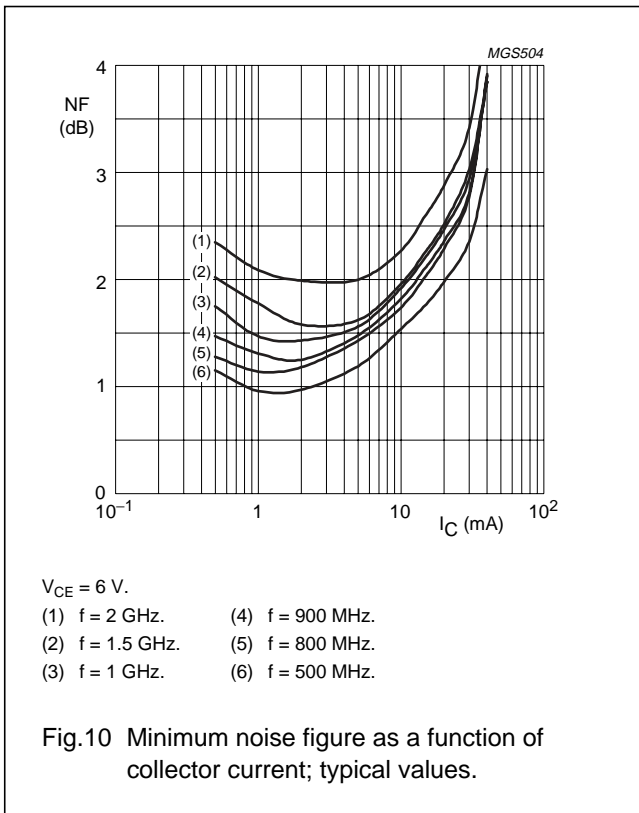
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UHF wideband transistor

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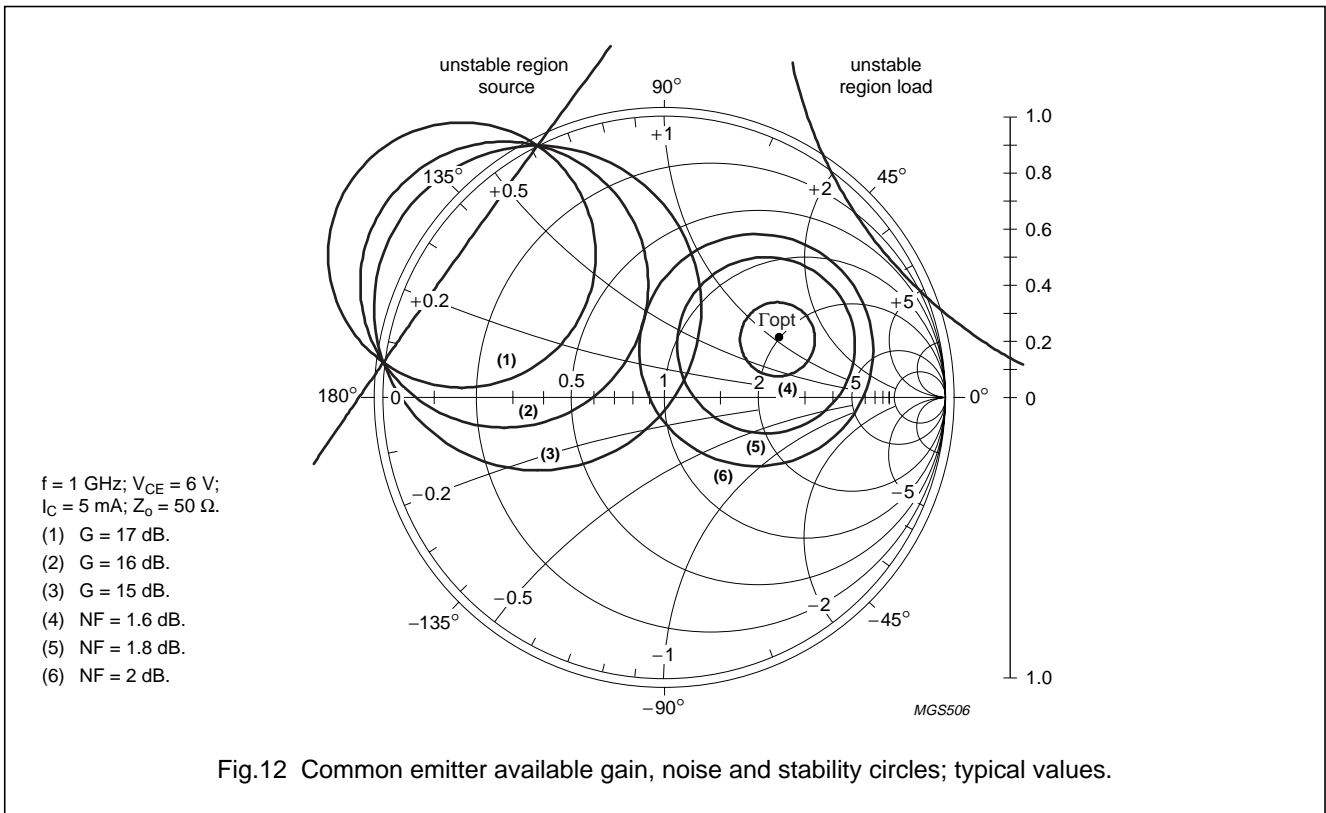


Fig.12 Common emitter available gain, noise and stability circles; typical values.

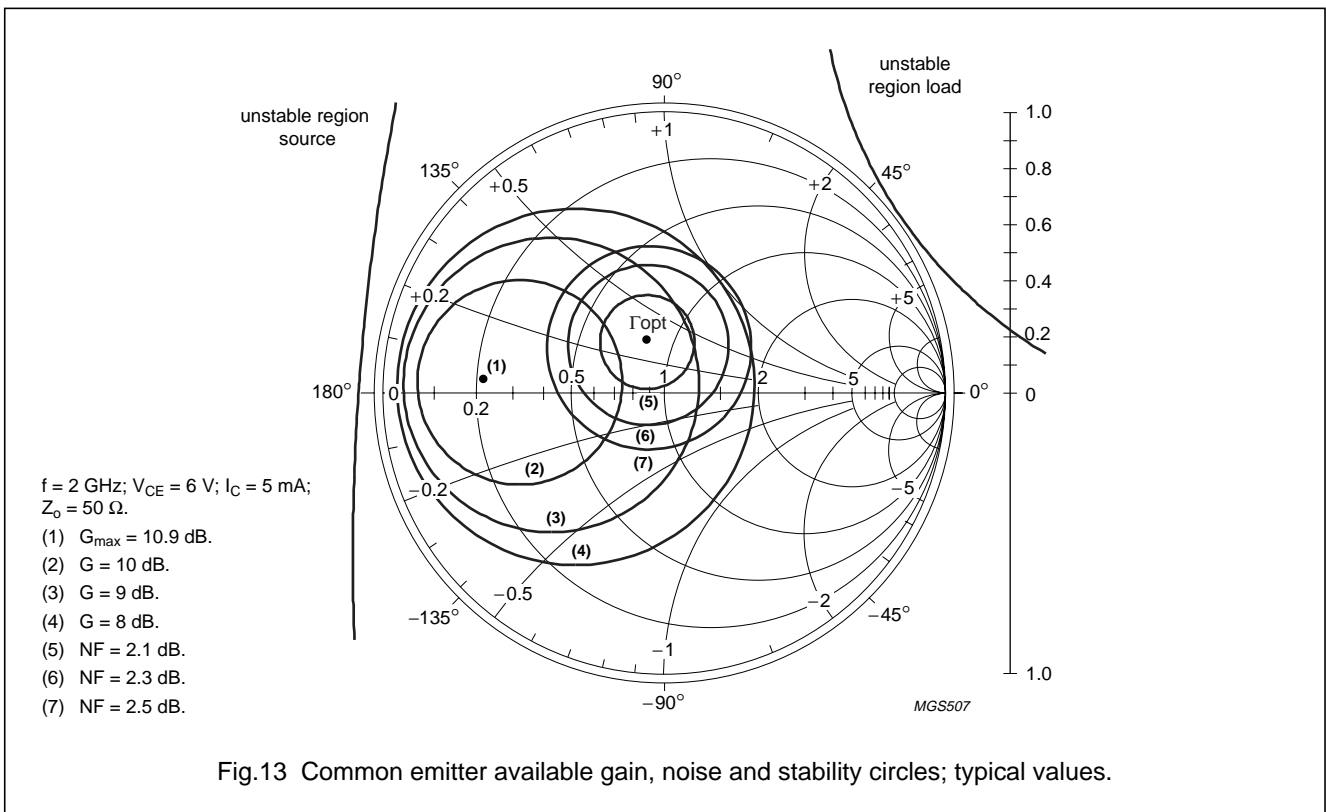
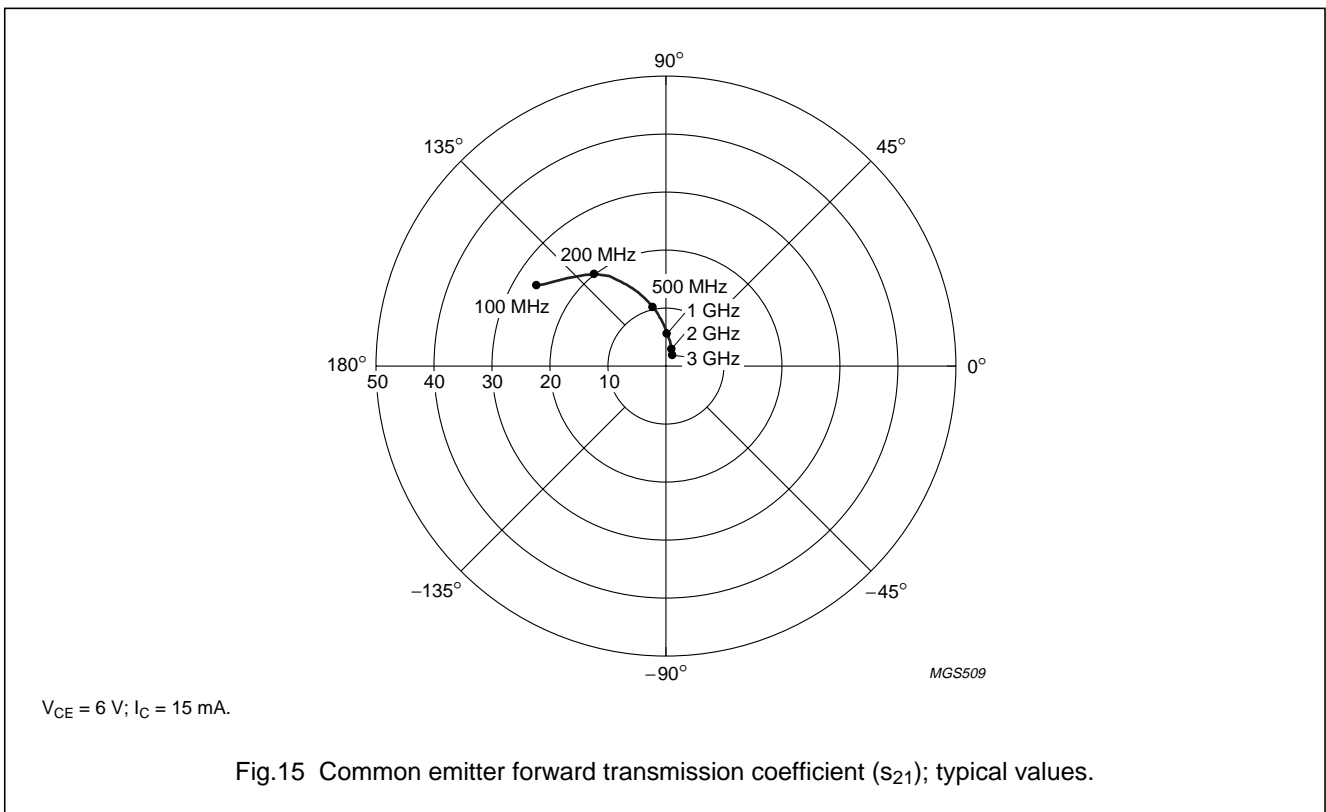
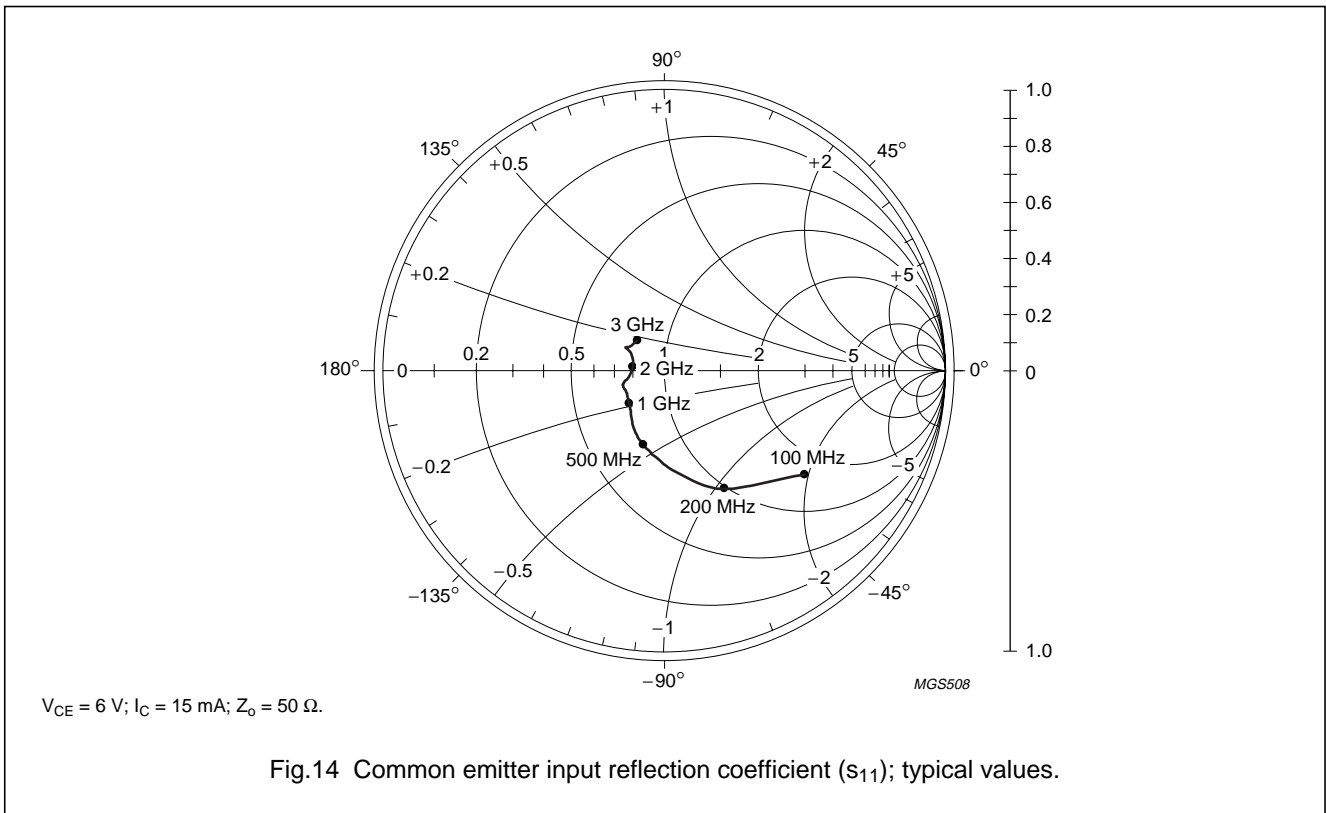


Fig.13 Common emitter available gain, noise and stability circles; typical values.

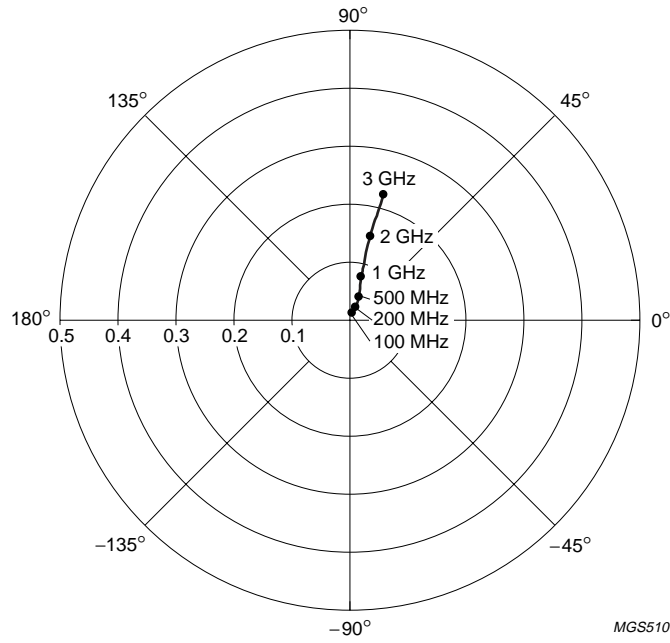
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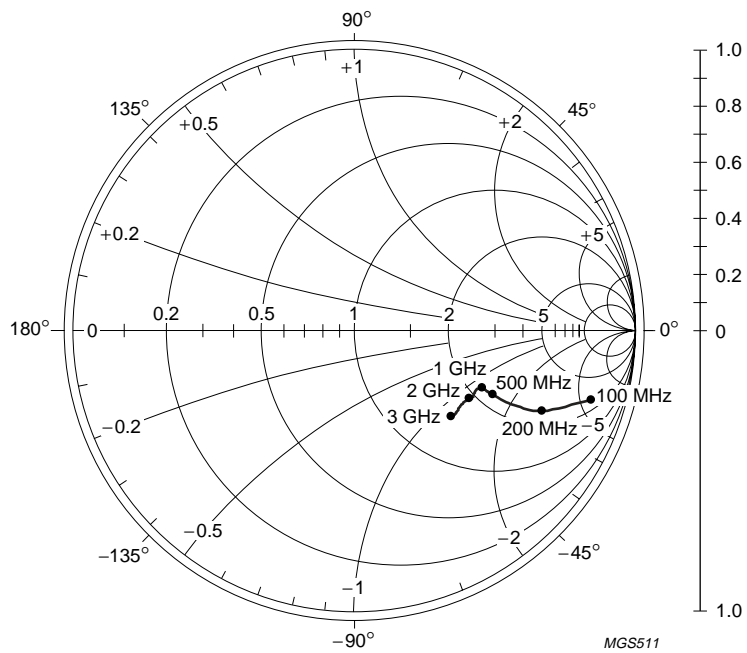
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$V_{CE} = 6\text{ V}; I_C = 15\text{ mA}$.

Fig.16 Common emitter reverse transmission coefficient (s_{12}); typical values.



$V_{CE} = 6\text{ V}; I_C = 15\text{ mA}; Z_0 = 50\ \Omega$.

Fig.17 Common emitter output reflection coefficient (s_{22}); typical values.

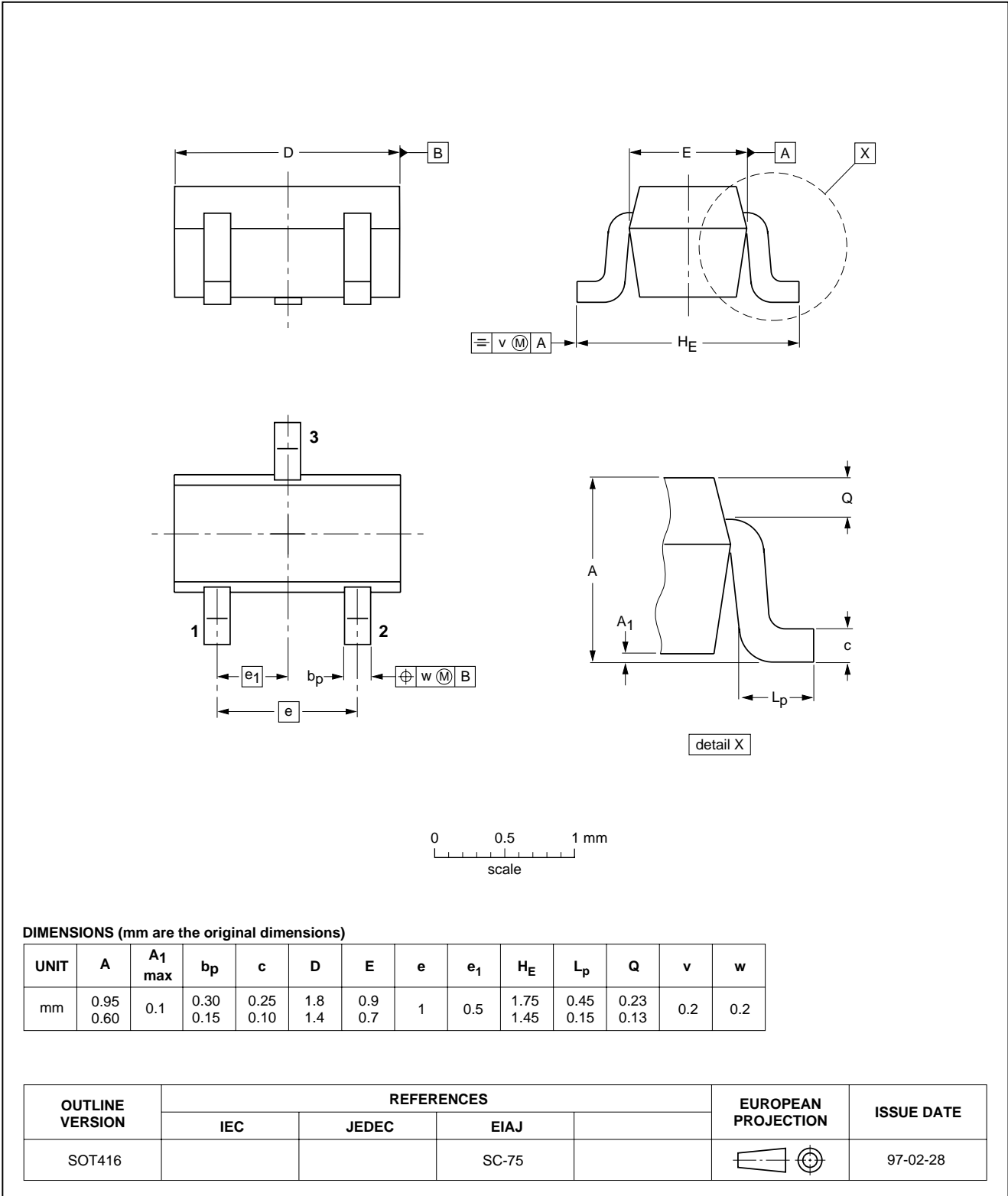
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT416



UHF wideband transistor

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DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS ⁽¹⁾
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

Note

1. Please consult the most recently issued data sheet before initiating or completing a design.

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NOTES

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NOTES

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